Si Photo Diode Chip--ORT-2124PD

1. Scope：

- The specification applies to NIP silicon photo diode chips.
- Type：ORT-2124PD

2. Structure：

- NIP planar type.
- Top（Cathode）Side：aluminum（Al）alloy.
- Back（Anode）Side：silver（Ag） alloy.

3. Size：(24mil×24mil)

- Chip size ：(600μm × 600μm) ± 40μm
- Chip thickness ：280μm ± 20μm
- Active area ：(460μm × 460μm) ± 20μm
- Pad size ：(120μm×120μm)± 10μm
- Pattern drawing：per fig. 1

4. Electro-Optical Characteristics：

(Ta=+25℃）

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward voltage	V_F	I_F=10mA, H=0	0.5		1.3	V
Reverse Breakdown voltage	V_{BR}	I_R=100μA, H=0	35			V
Reverse Dark Current	I_D	V_R=10V, H=0			10	nA
Light Current	I_L	V_R=5V,Has 1mw/cm^2,@ 940nm		9		μA
Peak Sensing wavelength	λ_P			940		nm
Junction Capacitance	C_J	V_R=3V, F=1MHz		3		pF

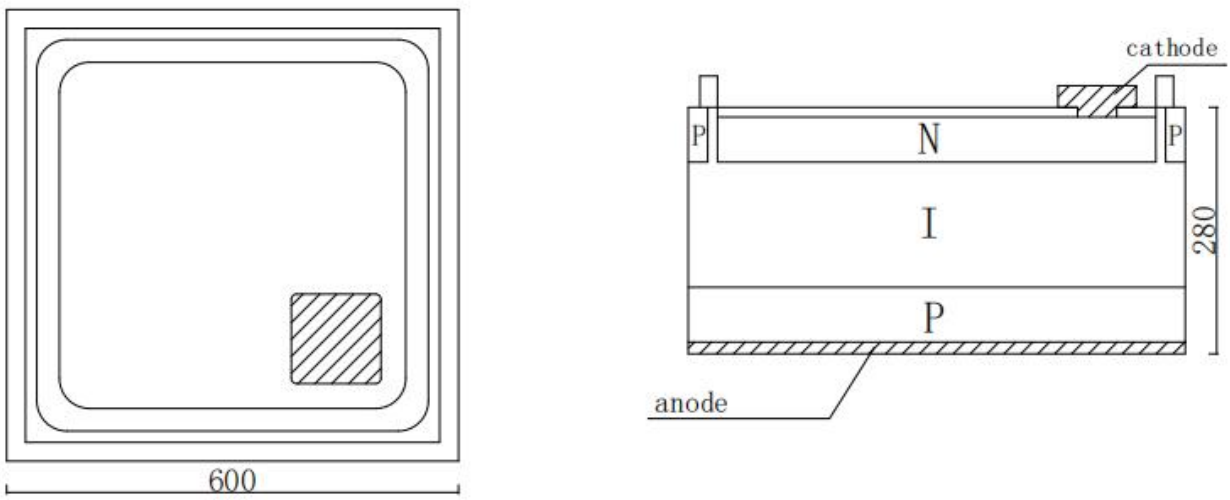

fig.1

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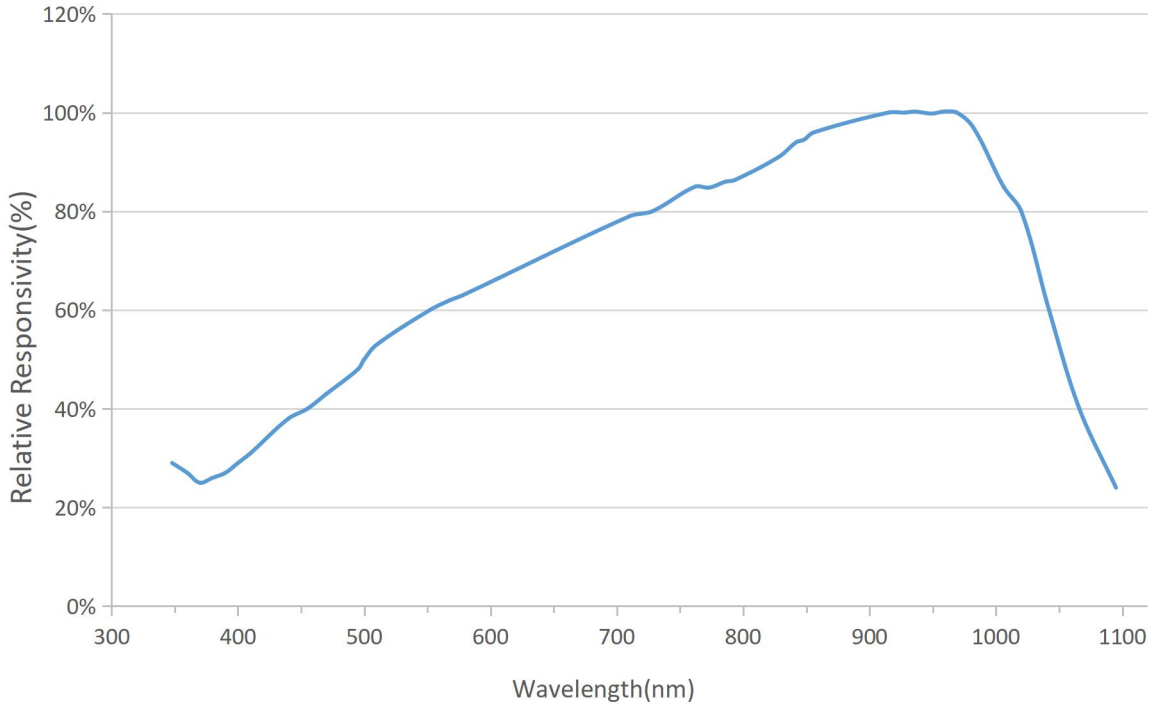
5. Spectral Response



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